

YTF542 Transistors

N-Channel Enhancement MOSFET

Military/High-Rel N

$V_{(BR)DSS}$ (V) 100

$V_{(BR)GSS}$ (V) 20

$I_{(D)}$ Max. (A) 24

$I_{(DM)}$ Max. (A) Pulsed $I_{(D)}$ 15

@Temp ($^{\circ}C$) 100#

IDM Max (@25 $^{\circ}C$ Amb) 96

@Pulse Width (s) (Condition)

Absolute Max. Power Diss. (W) 125

Minimum Operating Temp ($^{\circ}C$) -55

Maximum Operating Temp ($^{\circ}C$) 150 $\ddot{o}$

Thermal Resistance Junc-Case 1.0

Thermal Resistance Junc-Amb. 80

$V_{(GS)th}$ Max. (V) 4.0

$V_{(GS)th}$ (V) (Min) 2.0

@ $V_{(DS)}$ (V) (Test Condition) 20

@ $I_{(D)}$ (A) (Test Condition) 250u

$I_{(DSS)}$ Max. (A) 250u

@ $V_{(DS)}$ (V) (Test Condition) 100

@Temp ($^{\circ}C$) (Test Condition) 25#

$I_{(GSS)}$ Max. (A) 500n